

*Exceptional service in the national interest*



## **A roadmap for the integration of metal–organic frameworks with electronic devices and chemical sensors – Part 1**

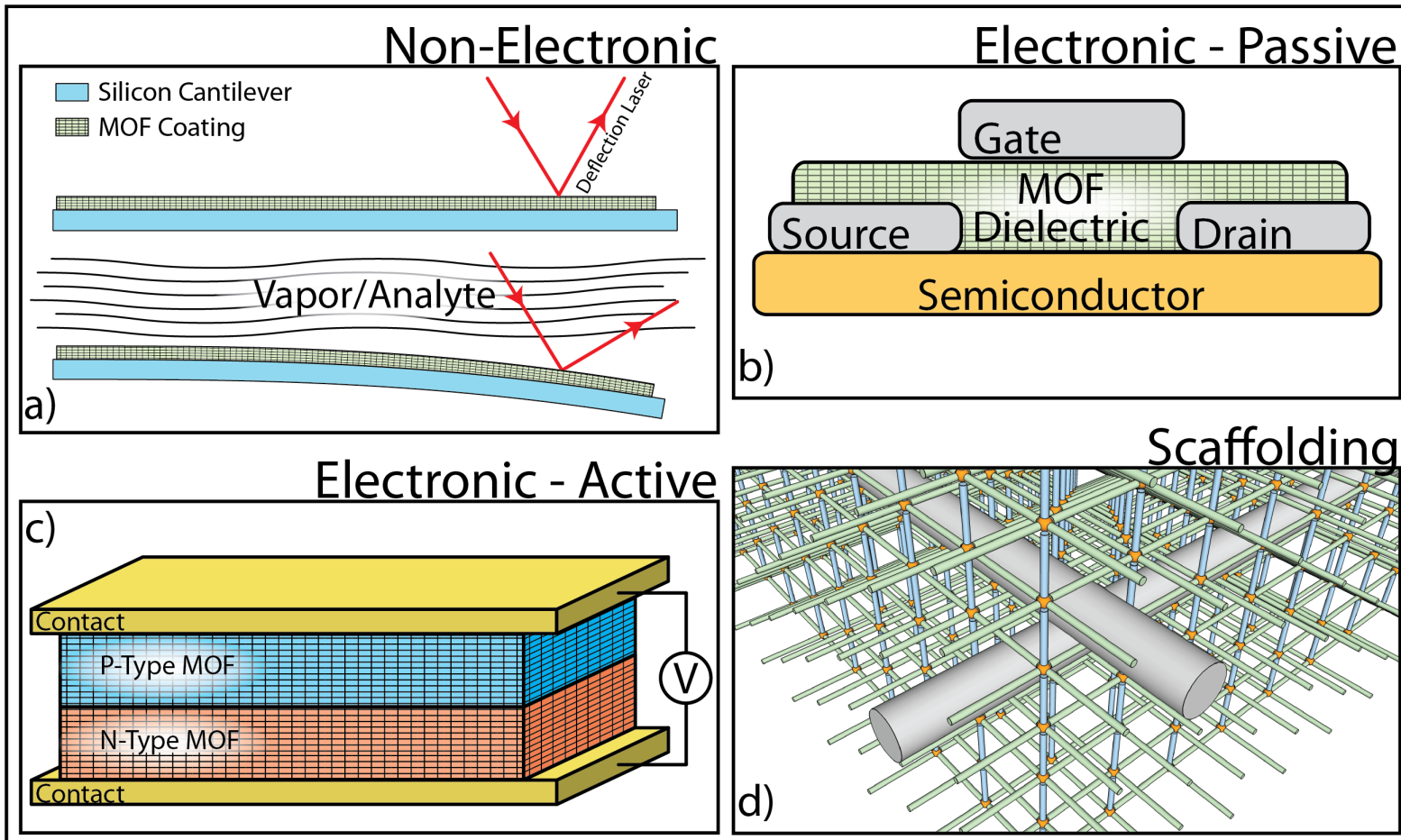
**Dr. Mark D. Allendorf**

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# Potential functions of MOFs within electronic and microelectromechanical systems (MEMS)

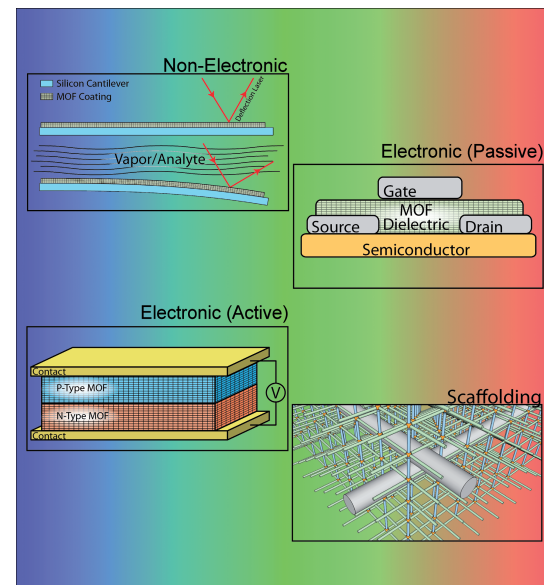
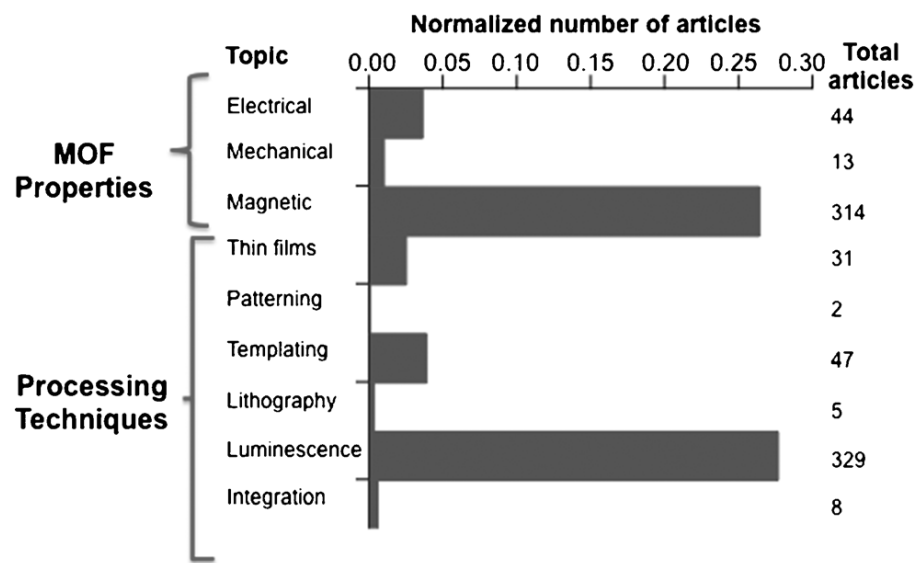


# First “roadmap” for MOFs as electronic materials in 2011

- MOF research dominated by gas storage and separations
- Focus was on synthesizing new MOFs and determining their properties:
  - Magnetic
  - Luminescence
- Processing techniques very limited:
  - Thin films (31 papers)
  - Patterning (2 papers)
  - Integration (8 papers)

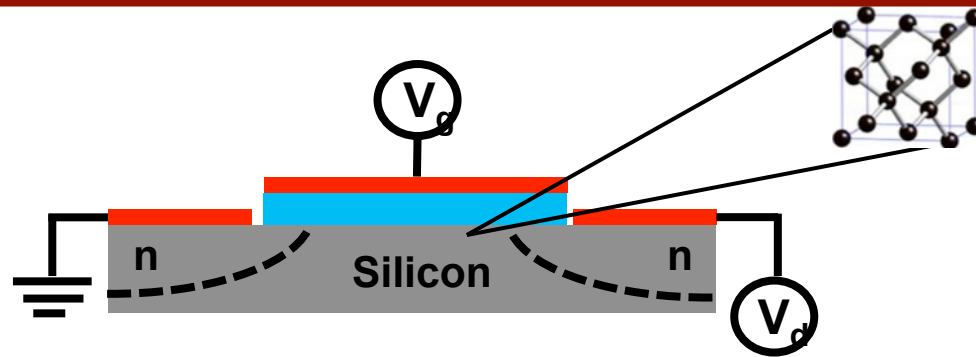
## 2011 Roadmap topics:

- Fundamental properties
- Thin-film growth and processing
- MOF hybrids and multilevel structures
- Device integration
- Manufacturing issues



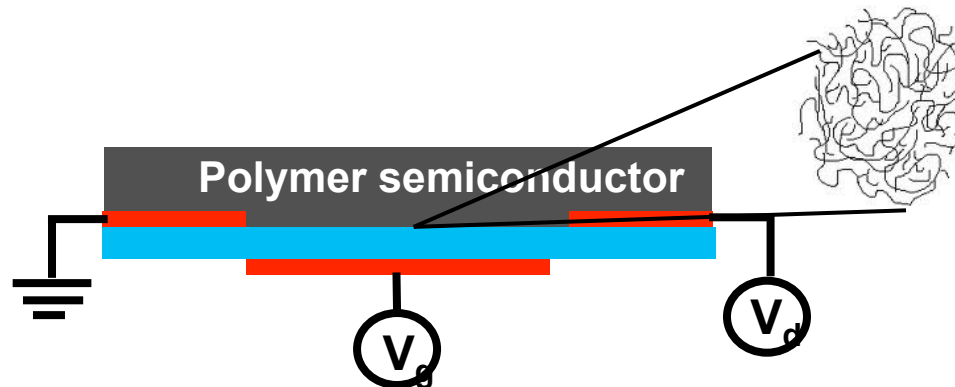
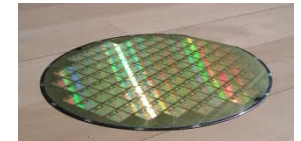
Allendorf, Schwartzberg, Stavila, Talin  
*Chem. Eur. J.* 2011, **17**, 11372

# MOFs as electronic materials provide a new dimension for device design: nanoporosity



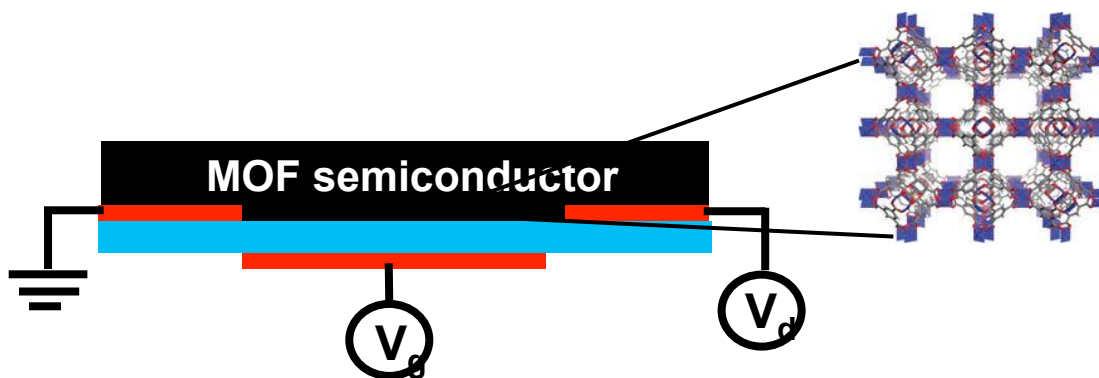
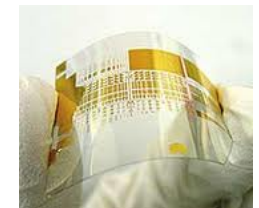
## Crystalline inorganic conductor

- High mobility
- Stability
- High cost
- Non-flexible
- Radiation damage



## Disordered organic conductor

- Flexible
- Tunable w/ chemistry
- Low cost fabrication
- Poor mobility
- Instability
- Low free carrier densities

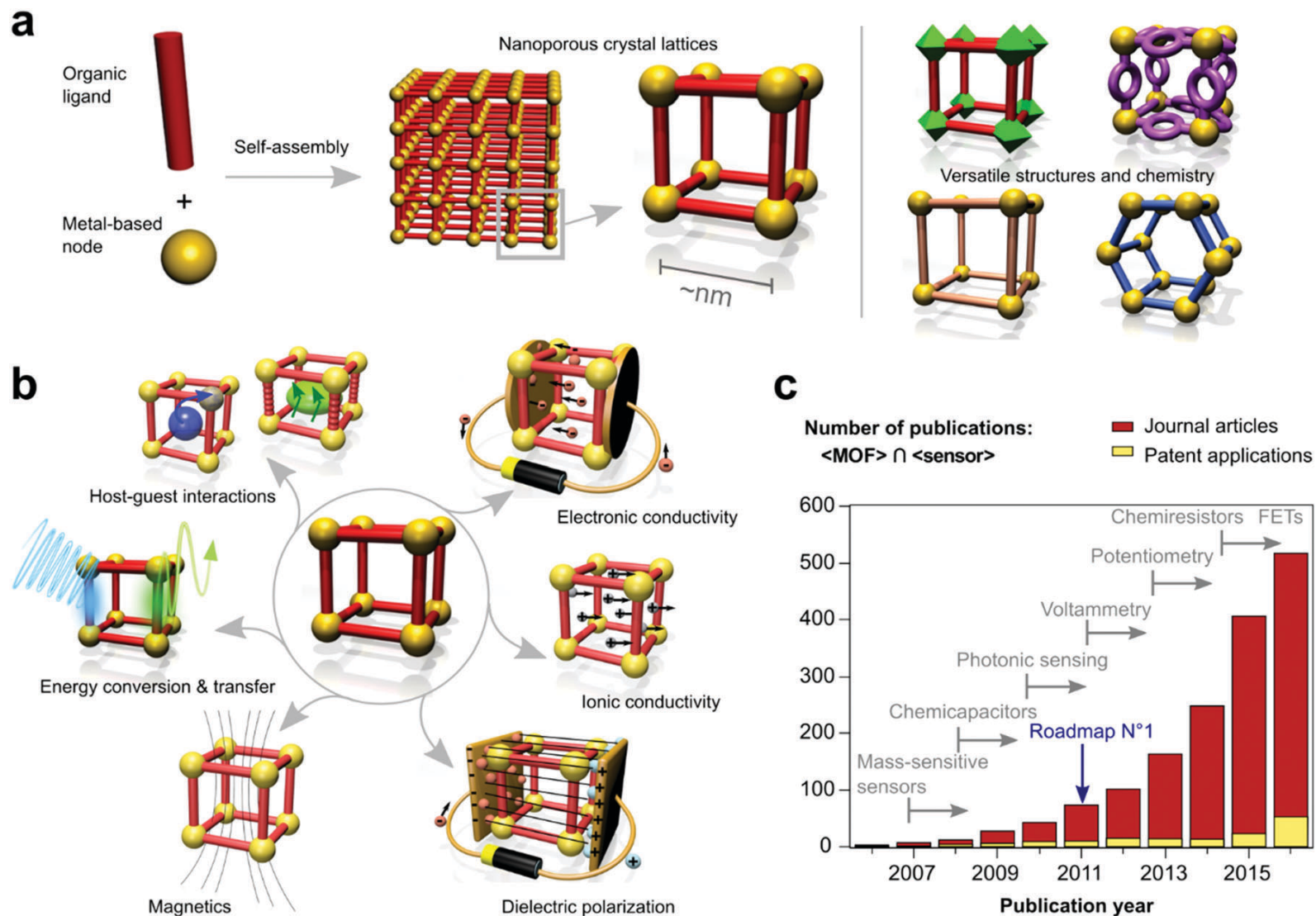


## Crystalline MOF conductor

- Structurally flexible
- Tunable w/ chemistry
- Scalable to nanometers
- Low cost fabrication
- Reconfigurable electronics
- Rad-hard
- Novel electronic material

*MOFs combine features of inorganic and organic materials*

# MOFs offer exceptional synthetic versatility for tuning not only pore size and chemistry, but also electronic structure



# We updated the MOF Electronic Roadmap in 2017

Chem Soc Rev



REVIEW ARTICLE

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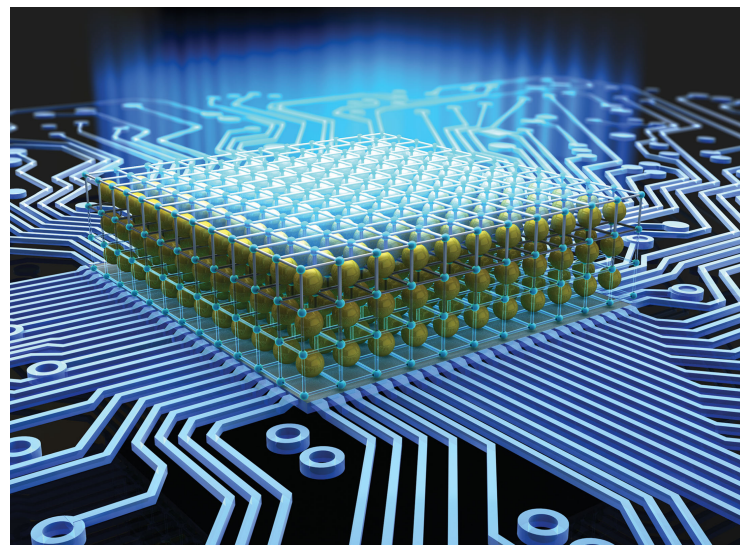


**An updated roadmap for the integration of metal–organic frameworks with electronic devices and chemical sensors**

Cite this: *Chem. Soc. Rev.*, 2017, 46, 3185

Ivo Stassen,<sup>ab</sup> Nicholas Burtch,<sup>b</sup> Alec Talin,<sup>c</sup> Paolo Falcaro,<sup>de</sup> Mark Allendorf<sup>f</sup> and Rob Ameloot<sup>ba</sup>

***Chem.Soc.Rev.*, 2017, 46, 3185**

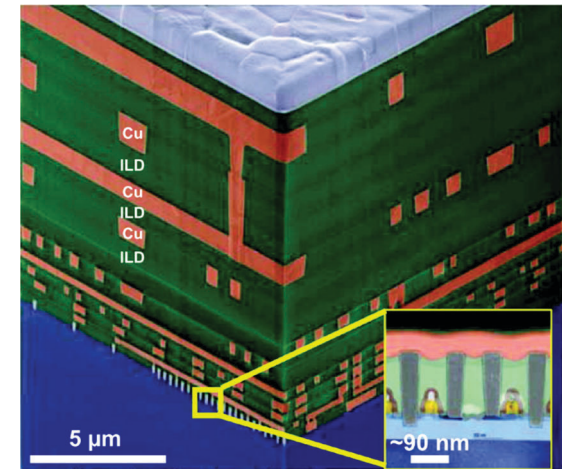


- Highlights research aimed at implementing MOFs as an integral part of solid-state microelectronics and sensors
- Manufacturing these devices will critically depend on the compatibility of MOFs with existing fabrication protocols and predominant standards
- This implies a shift from the microcrystalline powder synthesis in chemistry labs, towards film deposition and processing in a cleanroom environment
- Critical directions for future research are proposed to stimulate the next steps towards MOF-based microelectronics within the community

# Dielectrics: low-k and high-k

$\kappa$ : the resistance of a material to formation of an internal electric field

- Density, porosity, and less-polarizable atoms decrease  $\kappa$
- Low- $\kappa$  dielectrics:  $\kappa < 4$  ( $\text{SiO}_2$ )
  - Electrical insulator microelectronics
  - $\kappa = 2.3$  (0.1 MHz) ZIF-8
    - S. Eslava et al. *Chem. Mater.*, 2013, 25, 27
  - $\kappa = 2.4$  (0.1 MHz), 2D Sr(1,3-BDC) (pressed powder pellets)
    - M. Usman et al. *Mater. Chem. C*, 2014, 2, 3762
- High- $\kappa$  dielectrics:  $\kappa > 4$  ( $\text{SiO}_2$ )
  - Combined high-k, low electrical leakage and high breakdown voltage are needed in microelectronics to enable capacitive coupling
  - $\kappa = 19.5$  (106 Hz) interpenetrated Zn(dimethylammonium)(TBTC) framework, MOF-246.
    - W.-J. Li et al. *Nat. Commun.*, 2016, 7, 11830

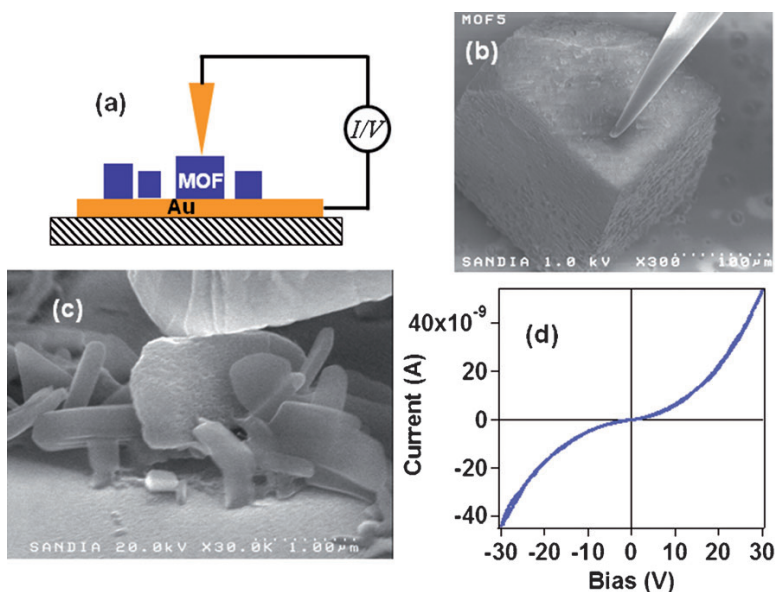


# Electrical conductivity: one of the most critical MOF properties requiring improvements

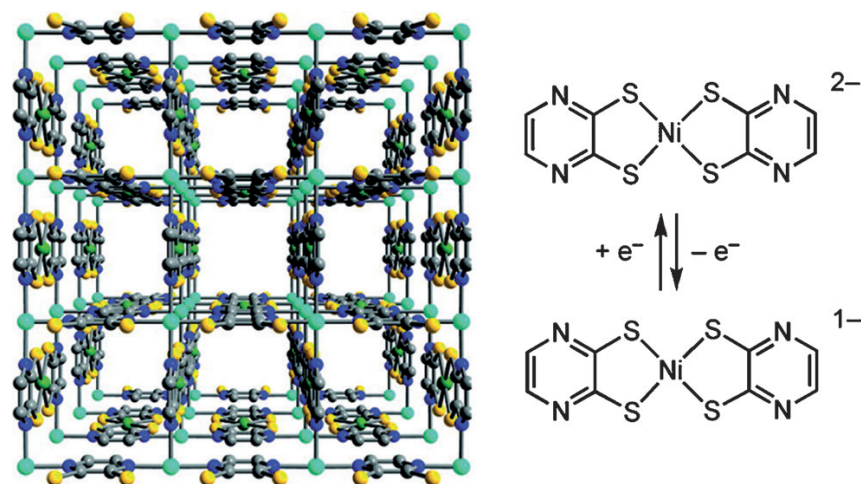
## Situation 2011:

- Conducting MOFs with permanent porosity: 1
- Insulating MOFs: thousands

Allendorf, Schwartzberg, Stavila, Talin  
*Chem. Eur. J.* 2011, **17**, 11372



Kobayashi, Jacobs, Allendorf, and Long  
*Chem. Mater.* 2010, **22**, 4120



# Situation in 2017: many more electrically conducting MOFs

Compound Formula	Conductivity <sup>[a,b]</sup> [S cm <sup>-1</sup> ]	Charge Mobility <sup>[b]</sup> [cm <sup>2</sup> V <sup>-1</sup> s <sup>-1</sup> ]	Activation Energy <sup>[c]</sup> [eV]	BET Surface Area <sup>[l]</sup>
Mn <sub>2</sub> (DSBDC) <sup>[50,52]</sup>	2.5 × 10 <sup>-12</sup> (pellet, 2-probe) <sup>[g,i]</sup>	0.01, <sup>[k]</sup> 0.02 <sup>[l]</sup> (TRMC/TOF)	0.81 (320–420 K) <sup>[e,j]</sup>	232 m <sup>2</sup> g <sup>-1</sup> <sup>[j]</sup>
Mn <sub>2</sub> (DOBDC) <sup>[52]</sup>	3.9 × 10 <sup>-13</sup> (pellet, 2-probe) <sup>[g,i]</sup>	N.R. <sup>[f]</sup>	0.54 (210–420 K) <sup>[e,j]</sup>	287 m <sup>2</sup> g <sup>-1</sup> <sup>[j]</sup>
Mn <sub>2</sub> (TTFTB) <sup>[73]</sup>	8.6 × 10 <sup>-5</sup> (crystal, 2-probe) <sup>[h]</sup>	N.R.	N.R.	594 m <sup>2</sup> g <sup>-1</sup>
Fe <sub>2</sub> (DSBDC) <sup>[52]</sup>	3.9 × 10 <sup>-6</sup> (pellet, 2-probe) <sup>[g,i]</sup>	N.R.	0.28 (200–420 K) <sup>[e,j]</sup>	470 m <sup>2</sup> mmol <sup>-1</sup>
Fe <sub>2</sub> (DOBDC) <sup>[52]</sup>	3.2 × 10 <sup>-7</sup> S cm <sup>-1</sup> (pellet, 2-probe) <sup>[g,i]</sup>	N.R.	0.38 (200–420 K) <sup>[e,j]</sup>	54 m <sup>2</sup> g <sup>-1</sup> <sup>[j]</sup>
Fe(1,2,3-triazolate) <sub>2</sub> <sup>[53]</sup>	7.7 × 10 <sup>-5</sup> (pellet, 4-probe) <sup>[e]</sup>	N.R.	N.R.	241 m <sup>2</sup> g <sup>-1</sup> <sup>[j]</sup>
(NBu <sub>4</sub> ) <sub>2</sub> Fe <sub>2</sub> (dhbq) <sub>3</sub> <sup>[95]</sup>	0.16 (pellet, 2-probe) <sup>[g]</sup>	N.R.	0.11 (70–300 K) <sup>[g]</sup>	450 m <sup>2</sup> g <sup>-1</sup>
Na <sub>0.9</sub> (NBu <sub>4</sub> ) <sub>1.8</sub> Fe <sub>2</sub> (dhbq) <sub>3</sub> <sup>[95]</sup>	6.2 × 10 <sup>-3</sup> (pellet, 2-probe) <sup>[g]</sup>	N.R.	0.18 (70–300 K) <sup>[g]</sup>	N.R.
Co <sub>2</sub> (TTFTB) <sup>[73]</sup>	1.5 × 10 <sup>-5</sup> (crystal, 2-probe) <sup>[h]</sup>	N.R.	N.R.	665 m <sup>2</sup> g <sup>-1</sup>
Ni <sub>3</sub> (HITP) <sub>2</sub> <sup>[88]</sup>	2 (pellet, 2-probe) <sup>[h]</sup> 40 (film, van der Pauw) <sup>[e]</sup>	N.R.	N.R.	531 m <sup>2</sup> mmol <sup>-1</sup>
Ni <sub>3</sub> (BHT) <sub>2</sub> <sup>[83,84]</sup>	0.15 (pellet, 2-probe) <sup>[e,m]</sup> 2.8 (microflake, van der Pauw) <sup>[e,m]</sup> 160 (microflake, van der Pauw) <sup>[e,n]</sup>	N.R.	0.026 <sup>[e,m]</sup> 0.010 <sup>[e,n]</sup>	N.R.
Cu <sub>3</sub> (HITP) <sub>2</sub> <sup>[89]</sup>	0.2 (pellet, 2-probe) <sup>[h]</sup>	N.R.	N.R.	N.R.
Cu <sub>3</sub> (HHTP) <sub>2</sub> <sup>[82]</sup>	0.2 (crystal, 4-probe)	N.R.	N.R.	N.R.
Cu <sub>3</sub> (BHT) <sub>2</sub> <sup>[28]</sup>	1580 (film, 4-probe) <sup>[e]</sup>	99 (hole, FET)	0.00206 (300 K)	N.R.
Cu[Cu(pdt) <sub>2</sub> ] <sup>[36]</sup>	6 × 10 <sup>-4</sup> (N.R.)	116 (electron, FET)	0.00012 (40 K) <sup>[e]</sup>	N.R.
Cu[Ni(pdt) <sub>2</sub> ] <sup>[37]</sup>	1 × 10 <sup>-8</sup> (film, 2-probe) <sup>[g]</sup>	N.R.	0.193 (200–400 K)	N.R.
Cu[Ni(pdt) <sub>2</sub> ] <sub>(I<sub>2</sub>-doped)</sub> <sup>[37]</sup>	1 × 10 <sup>-4</sup> (film, 2-probe) <sup>[g]</sup>	N.R.	0.49 (film, 2-probe) <sup>[g]</sup>	385 m <sup>2</sup> g <sup>-1</sup>
TCNQ@Cu <sub>3</sub> (BTC) <sub>2</sub> <sup>[56]</sup>	0.07 (film, 4-probe)	N.R.	0.18 (film, 2-probe) <sup>[g]</sup>	N.R.
Zn <sub>2</sub> (TTFTB) <sup>[72,73]</sup>	4.0 × 10 <sup>-6</sup> (crystal, 2-probe) <sup>[m]</sup>	0.2 (TRMC/TOF)	0.041 (125–300 K)	214 m <sup>2</sup> g <sup>-1</sup>
NNU-27 <sup>[96]</sup>	1.3 × 10 <sup>-3</sup> (crystal, 2-probe)	N.R.	N.R.	662 m <sup>2</sup> g <sup>-1</sup>
Pd <sub>3</sub> (BHT) <sub>2</sub> <sup>[85]</sup>	2.8 × 10 <sup>-2</sup> (film, 4-probe)	N.R.	N.R.	537 m <sup>2</sup> mmol <sup>-1</sup>
Cd <sub>2</sub> (TTFTB) <sup>[73]</sup>	2.9 × 10 <sup>-4</sup> (crystal, 2-probe) <sup>[h]</sup>	N.R.	N.R.	N.R.
[In(isophthalate) <sub>2</sub> ] <sup>-</sup> <sup>[75]</sup>	N.R.	4.6 × 10 <sup>-3</sup> (FET) <sup>[h]</sup>	N.R.	559 m <sup>2</sup> g <sup>-1</sup>
Pt <sub>3</sub> (HTTP) <sub>2</sub> <sup>[86]</sup>	10 <sup>-6</sup> (pellet, 2-probe) <sup>[p]</sup>	N.R.	N.R.	521 m <sup>2</sup> mmol <sup>-1</sup>
				391 m <sup>2</sup> g <sup>-1</sup>

# Charge transport properties of conducting MOFs are still relatively poor

Material or formula unit	Conductivity (S cm <sup>-1</sup> )	Charge carrier <sup>e</sup>	Mobility (cm <sup>2</sup> V <sup>-1</sup> s <sup>-1</sup> )
Copper	10 <sup>5</sup> -10 <sup>6</sup>	e	46
Doped polyacetylene	560 (n); 360 (p)	h or e	1 (n-doped, <i>cis</i> )
Undoped polyacetylene	10 <sup>-9</sup>		
Doped polyaniline	10 <sup>3</sup>		
Graphene	550 <sup>b</sup>		
Polycrystalline graphite	1250		
Polythiophenes	1975	h	1-10
Rubrene			4
TTF-TCNQ	700		
Cu[Ni(PDT) <sub>2</sub> ] (I <sub>2</sub> doped)	1 × 10 <sup>-4 a</sup>		
Cu <sub>3</sub> (BHT) <sub>2</sub> <sup>d</sup>	1580 <sup>b</sup>	h or e	99 (h); 116 (e)
Ni <sub>3</sub> (HITP) <sub>2</sub>	2; <sup>a</sup> 40 <sup>b</sup>	h or e	48.6
Ni <sub>3</sub> (BHT) <sub>2</sub>	0.15; <sup>a</sup> 2.8-160 <sup>c</sup>		
Mn <sub>2</sub> (DOBDC)	3.9 × 10 <sup>-13 a</sup>		
Fe <sub>2</sub> (DOBDC)	3.2 × 10 <sup>-7 a</sup>		
Mn <sub>2</sub> (DSBDC)	1.2 × 10 <sup>-12 a</sup>		0.01
{[Cd <sub>2</sub> (AZBPY) <sub>2</sub> (HO-1,3-BDC) <sub>2</sub> ](AZBPY)(H <sub>2</sub> O)} <sub>n</sub>	1.86 <sup>b</sup>	e	
K <sub>1.2</sub> Ru <sub>3.6</sub> [Ru(CN) <sub>6</sub> ] <sub>3</sub> ·16H <sub>2</sub> O	5.7 × 10 <sup>-3</sup>		
TCNQ@Cu <sub>3</sub> (BTC) <sub>2</sub>	0.07 <sup>b</sup>	h	
TCNQ@[Cu(TPyP)Cu <sub>2</sub> (O <sub>2</sub> CCH <sub>3</sub> ) <sub>4</sub> ]	2.5 × 10 <sup>-6</sup>		
Zn <sub>2</sub> (TTFTB)	4.0 × 10 <sup>-6</sup>		0.2
Porphyrin Zn-SURMOF-2		h	0.002
Pd@porphyrin Zn-SURMOF-2		h	0.003-0.004
[Sr(HBTC)(H <sub>2</sub> O)] <sub>n</sub>	10 <sup>-9</sup> -10 <sup>-7 a</sup>		
NNU-7 (anthracene MOF)	1.3 × 10 <sup>-3 c</sup>		
(NBu <sub>4</sub> ) <sub>2</sub> Fe <sub>2</sub> (DHBQ) <sub>3</sub>	0.16 <sup>a</sup>		

# Ionic conductivity

## Advantages of MOFs as solid-state electrolytes:

- Regular pores allow efficient transport
- Anhydrous transport is feasible
- Thermal stability allows operation  $> 100\text{ }^\circ\text{C}$

## Proton transport [(a) in figure]

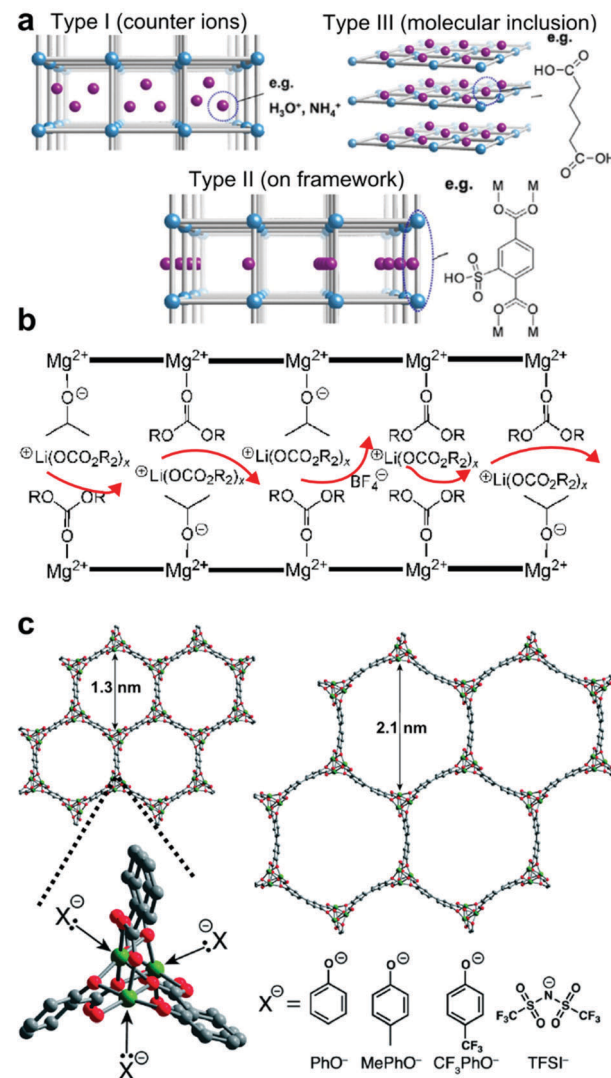
- Several strategies for introducing  $\text{H}^+$ :
  - Counterions as proton carriers
  - Acidic functional groups
  - Protonated guest molecules
- Triazole@sulfonated MOF:  $5 \times 10^{-4}\text{ S cm}^{-1}$  at  $150^\circ\text{C}$ 
  - J.A. Hurd et al. *Nat. Chem.* 2009

## $\text{Li}^+$ transport [(b) in figure]

- Li-alkoxide grafting: MOF-74  $0.012\text{ mS cm}^{-1}$ 
  - B. M. Wiers et al. *JACS*, 2011, 133, 14522
- UiO-66  $0.018\text{ mS cm}^{-1}$ 
  - R. Ameloot et al. *Chemistry*, 2013, 19, 5533

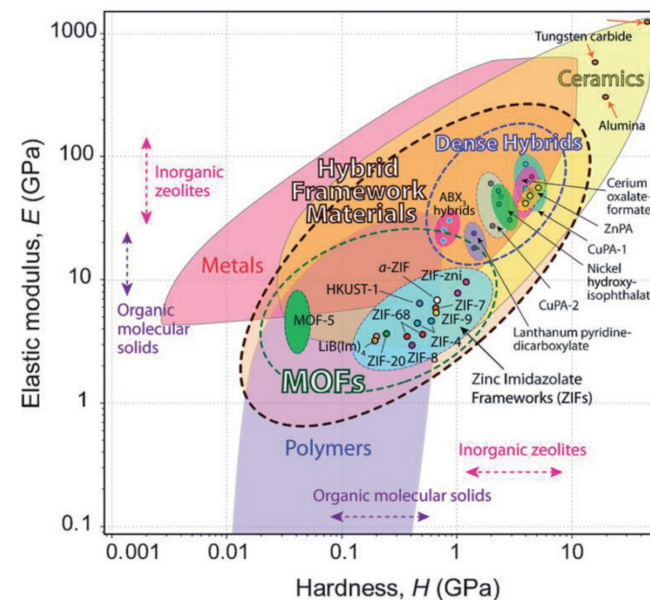
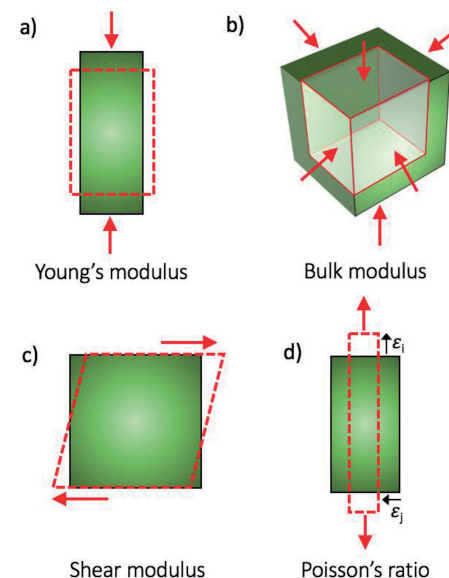
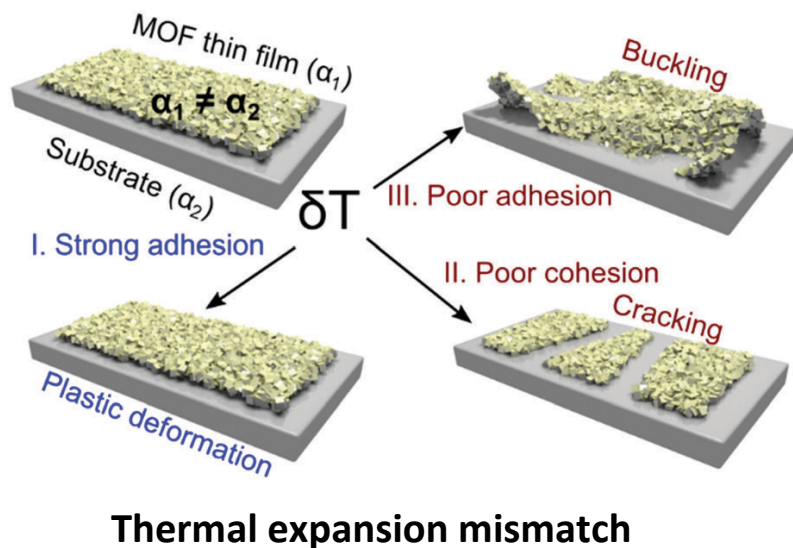
## $\text{Mg}^{2+}$ transport [(c) in figure]

- $0.25\text{ mS cm}^{-1}$ 
  - M.L. Aubrey *Energy Environ. Sci.*, 2014, 7, 667



# Mechanical and thermal properties

- MOFs are “soft” materials
- Thermal expansion is low
- Thermal conductivity
  - Negative thermal expansion common
  - TCE low compared with metals
- Anisotropy of bond strengths
- Structural flexibility leads to anomalous behaviors
- Structure-property relationships are being discovered

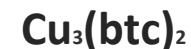
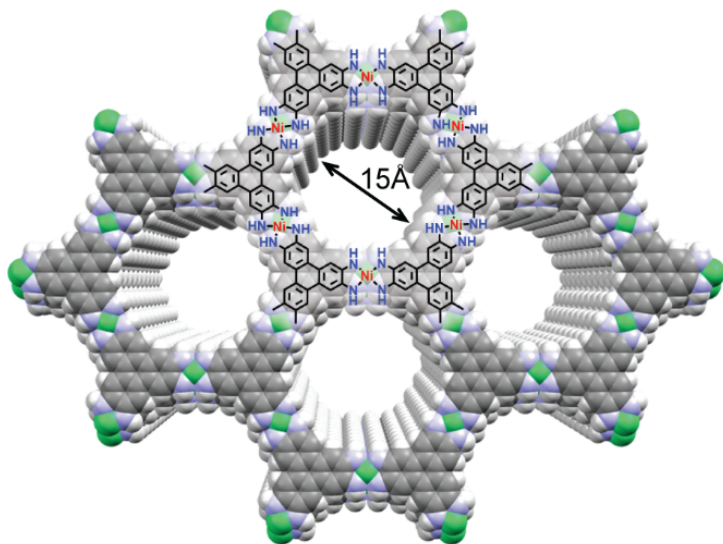


# MOF thermoelectric materials: two prototypes



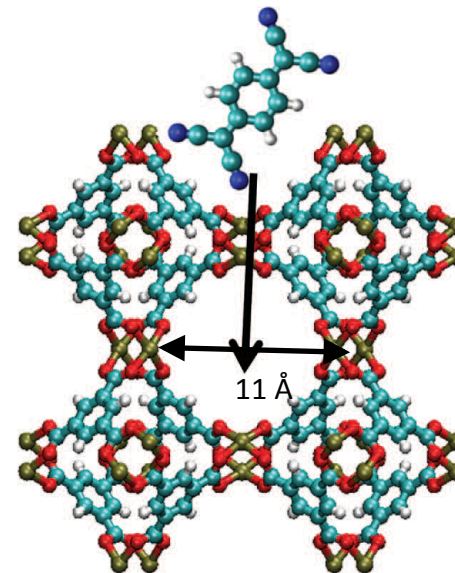
2D “Metal-Organic Graphene Analogue” (MOG)

L. Sun et al. *Joule* 2017



3D Metal-Organic Framework

K. Ericksson et al. *Adv. Mater.* 2015, 27, 3453



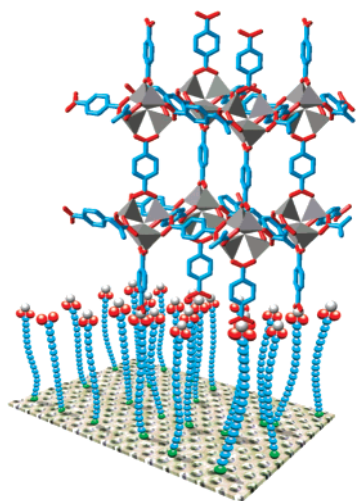
Material	Type	$\sigma$ (S/m)	$\kappa$ (W/m · K)	$S$ ( $\mu\text{V}/\text{K}$ )	$PF$ ( $\mu\text{W}/\text{m} \cdot \text{K}^2$ )	ZT (300K)
$\text{TCNQ}@Cu_3(\text{BTC})_2$	<i>p</i>	0.45	0.25	+400	0.06	$0.7 \times 10^{-4}$
$\text{Ni}_3(\text{HITP})_2$	<i>n</i>	58.8	0.2	-11.9	0.01	$1.2 \times 10^{-3}$

*How can we improve the thermoelectric properties of MOFs?*

# Integration and assembly to create electronic devices

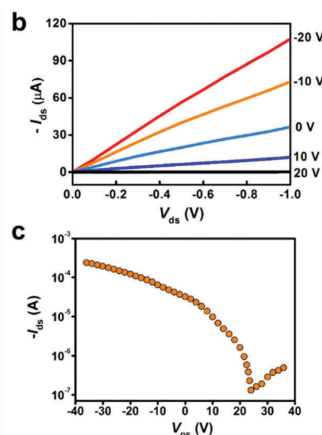
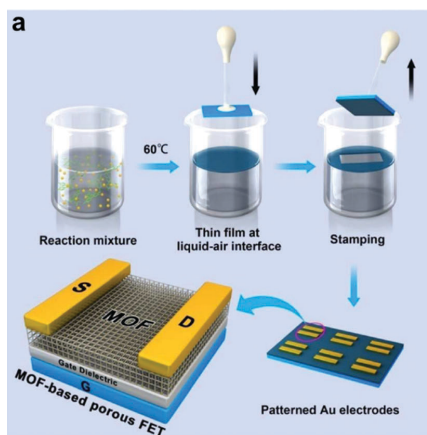
## MOF growth on patterned substrate

S. Hermes et al.  
*JACS* 2005, 127, 13744

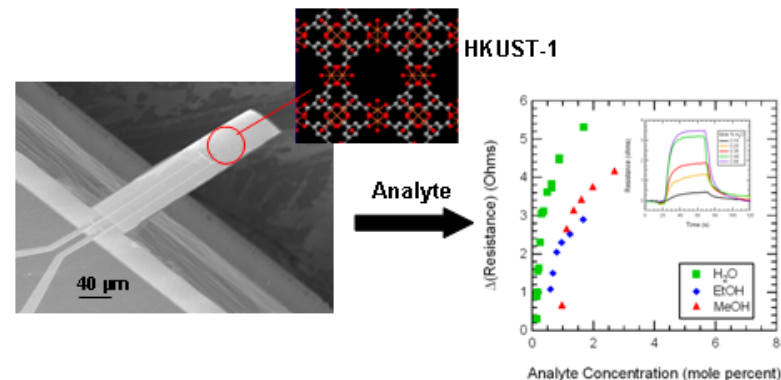


M. D. Allendorf et al.  
*JACS* 2008, 130, 14404

FET  
 $\text{Ni}_3(\text{HITP})_2$  MOG  
G. Wu et al. *JACS*, 2017, 139, 1360

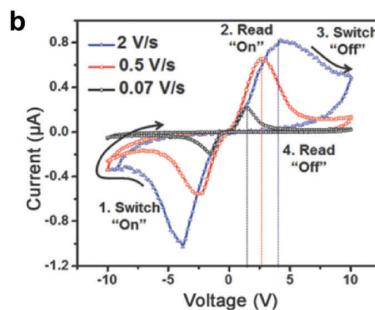


## MOF-coated Microcantilever



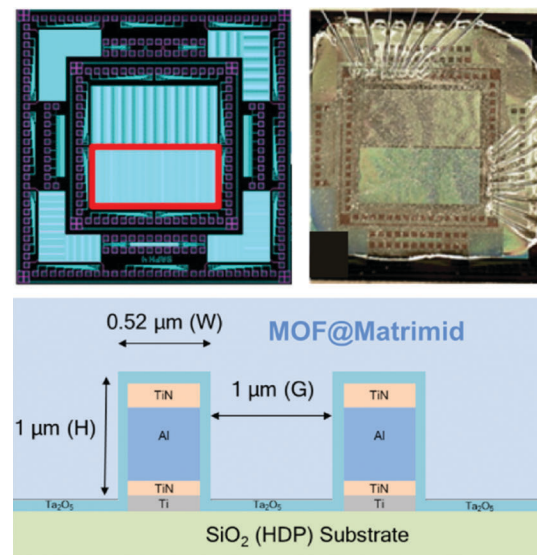
## Memristor

S. M. Yoon et al.  
*Ang. Chem. IE*, 2014, 53, 4437



## Chemicapacitor

S. Sachdeva et al.  
*ACS Sens.*, 2016, 1, 1188



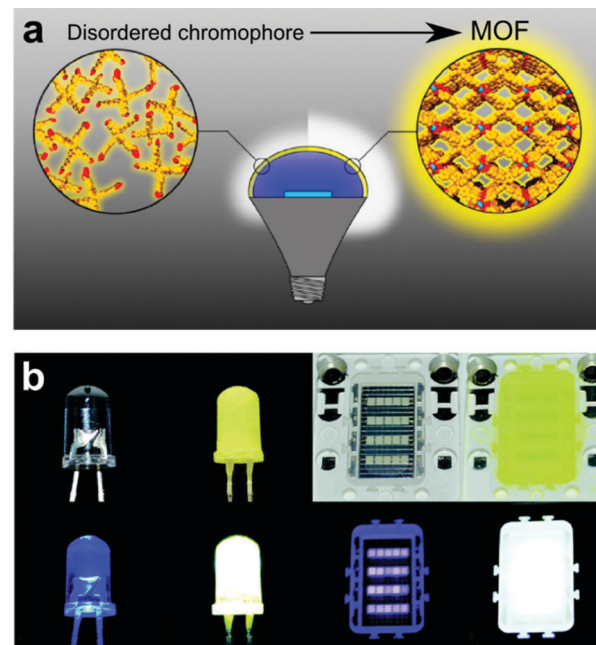
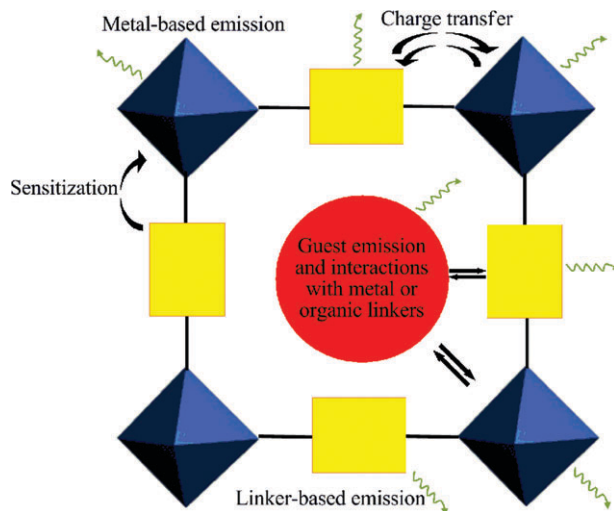
# Luminescent frameworks are the largest subclass of electronically relevant MOFs

## Many strategies

- Linker
- Metal ion
- Guest

## Applications

- Phosphors
- Chemical sensors
- Scintillators
- Thus far no semiconducting MOF as actual emitting layer

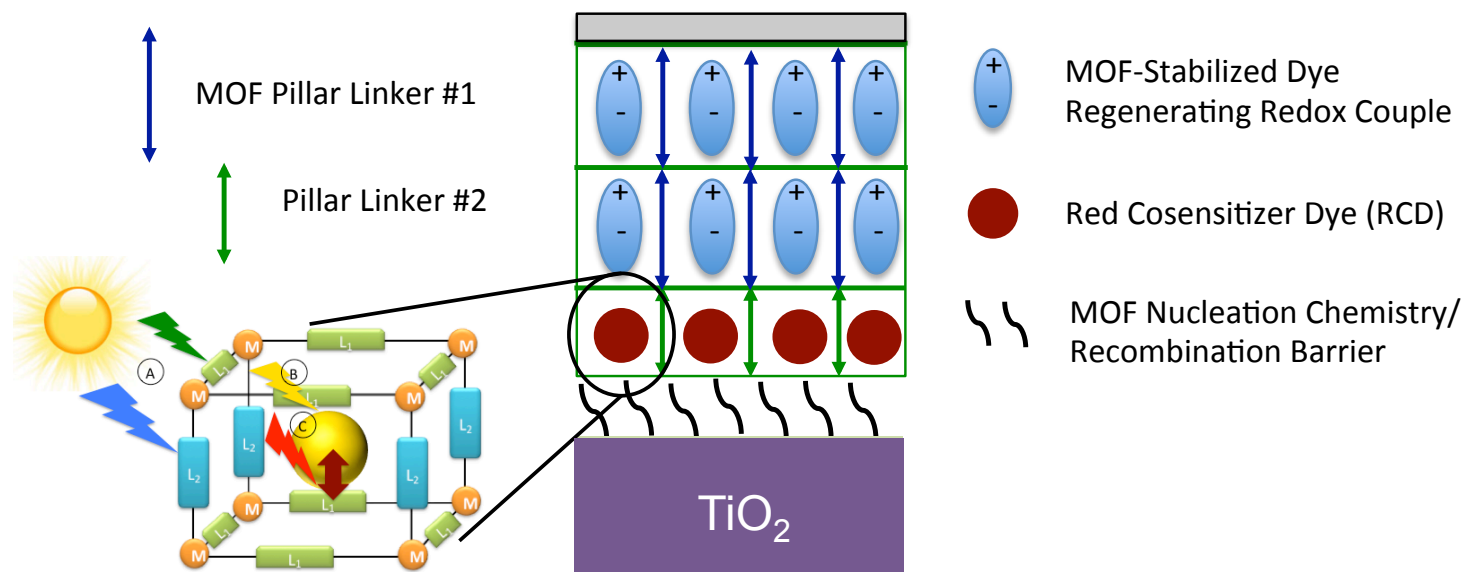


MOFs for light emitting devices. (a) Schematic illustration of the improvement in quantum yield of a yellow-emitting organic chromophore by incorporation in a rigid metal-organic framework. (W.P. Lustig et al. *Inorg. Chem.*, 2016, 55, 7250) (b) Blue LED bulb and plate coated with solution-processed Zn<sub>2</sub>(TCPBE) MOF phosphor as a demonstration of application in white LEDs (Z. Hu et al. *Chem. Commun.*, 2015, 51, 3045).

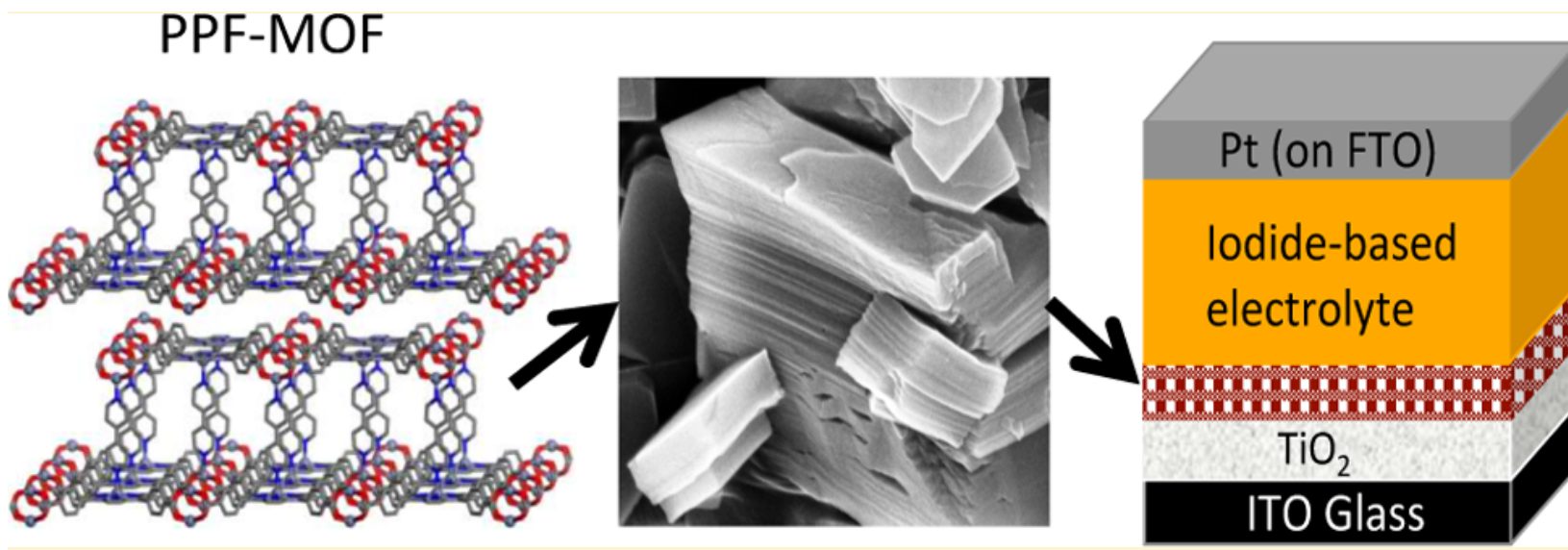
# Can Metal-Organic Frameworks (MOFs) address the challenges facing DSSC?

## Roles and advantages of MOFs in DSSCs

Challenge	MOF role
Light harvesting	Multiple linkers + guest molecules for broad solar coverage
Dye aggregation	Crystalline structure, confined guests prevent aggregation
Band offsets	Tunable linker and guest electronic structure
Stability/reliability	Rigidified, isolated linkers; confined electrolyte



# Integrating MOFs in DSSC devices



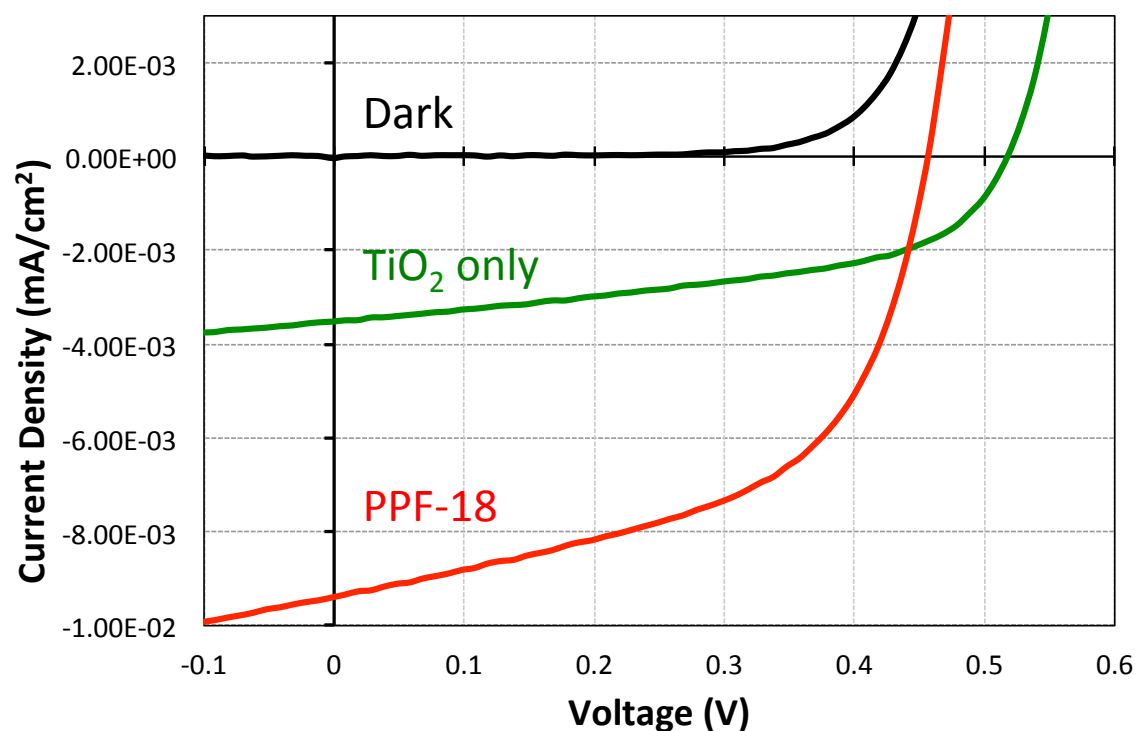
E. Spoerke et al. J. Phys. Chem. C 2017, 121, 4816

## Challenges:

- How do we incorporate MOFs into DSSCs as active layer materials?
- How do we know that the MOF is doing something?

# DSSC sensitized by MOF nanocrystals

## Reduced photocurrent in the absence of PPF-18



### AM 1.5 illumination

#### Averaged metrics:

$$V_{oc} \text{ (V)} = 0.537 \pm 0.023$$

$$J_{sc} \text{ (mA/cm}^2\text{)} = 0.00410 \pm 0.00090$$

$$FF = 0.486 \pm 0.014$$

$$\eta \text{ (\%)} = 0.00107 \pm 0.000233$$

$$V_{oc} \text{ (V)} = 0.425 \pm 0.029$$

$$J_{sc} \text{ (mA/cm}^2\text{)} = 0.00797 \pm 0.0012$$

$$FF = 0.548 \pm 0.014$$

$$\eta \text{ (\%)} = 0.00186 \pm 0.000338$$

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